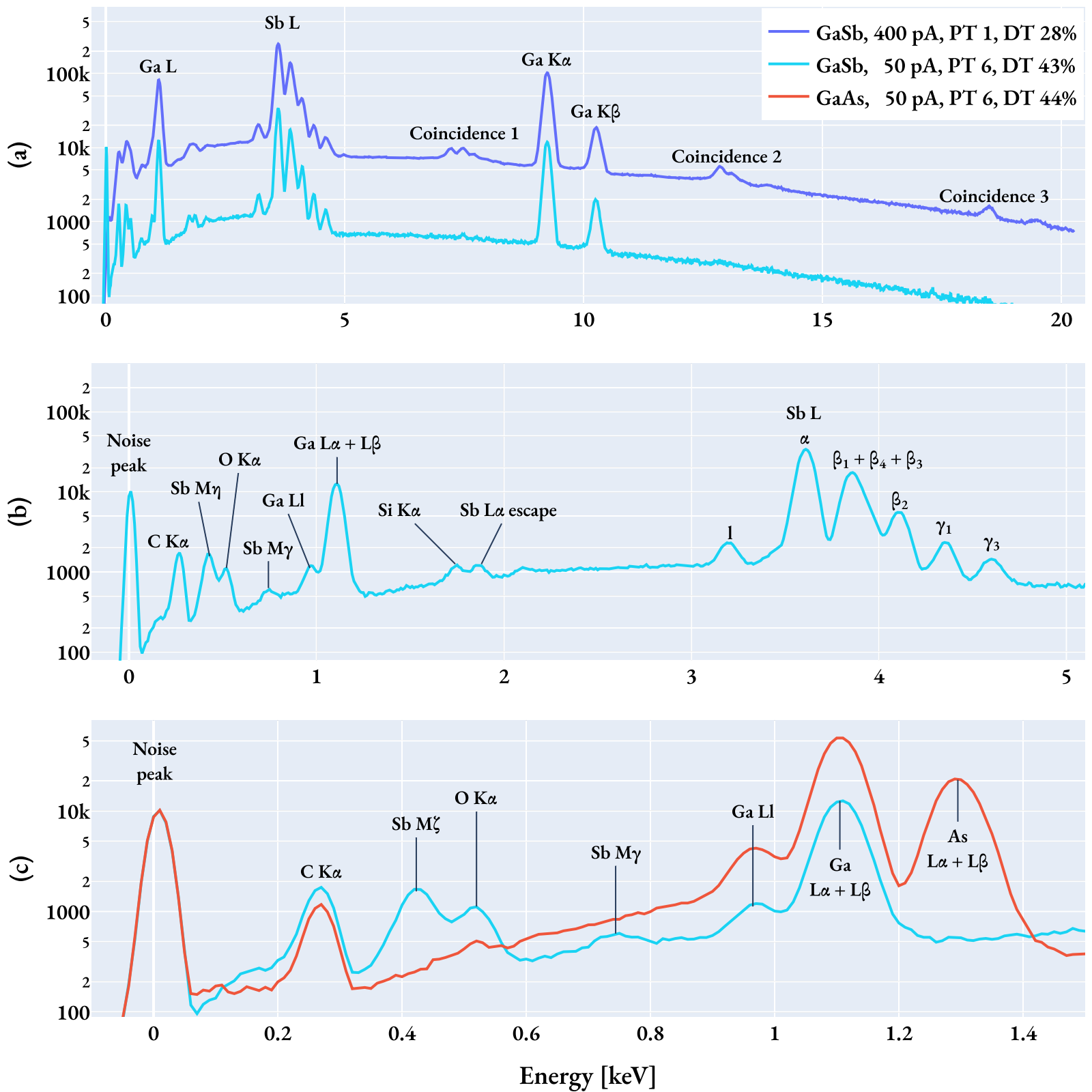
(a)
GaSb, 400 pA, PT 1, DT 28%
GaSb, 50 pA, PT 6, DT 43%
GaAs, 50 pA, PT 6, DT 44%
Ga L
Sb L
Ga Kα
Ga Kβ
Coincidence 1
Coincidence 2
Coincidence 3
(b)
Noise peak
C Kα
Sb Mη
O Kα
Sb Mγ
Ga Ll
Ga Lα + Lβ
Si Kα
Sb Lα escape
1
Sb L α
β1 + β4 + β3
β2
γ1
γ3
(c)
Noise peak
C Kα
Sb Mζ
O Kα
Sb Mγ
Ga Ll
Ga Lα + Lβ
As Lα + Lβ
Energy [keV]